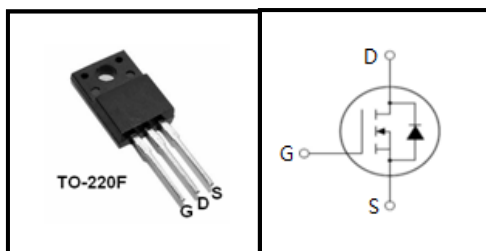


**FEATURES**

- Very low FOM  $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- RoHS compliant

**APPLICATIONS**

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information	
device	HCS65R170M
Package	TO-220F
Marking	HCS65R170M

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , unless otherwise noted				
Parameter	Symbol	Value		Unit
		TO-220F		
Drain-Source Voltage ( $V_{GS} = 0\text{V}$ )	$V_{DSS}$	650		V
Continuous Drain Current	$I_D$	$T_C = 25^\circ\text{C}$	20	
		$T_C = 100^\circ\text{C}$	12	
Pulsed Drain Current (note1)	$I_{DM}$	60		A
Gate-Source Voltage	$V_{GSS}$	$\pm 30$		V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	484		mJ
Avalanche Current (note1)	$I_{AR}$	3.5		A
Repetitive Avalanche Energy (note1)	$E_{AR}$	0.7		mJ
MOSFET $dv/dt$ ruggedness, $V_{DS} = 0 \dots 480\text{V}$	$dv/dt$	50		V/ns
Reverse diode $dv/dt$ , $V_{DS} = 0 \dots 480\text{V}$ , $I_{SD} \leq I_D$	$dv/dt$	15		V/ns
Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_D$	151	34	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150		$^\circ\text{C}$

Thermal Resistance				
Parameter	Symbol	Value		Unit
		TO-220F		
Thermal Resistance, Junction-to-Case	$R_{thJC}$	0.83	3.7	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	62	80	



Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	650	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 650V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	$\mu A$
		$V_{DS} = 650V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	100	
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 30V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	--	4.5	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 10A$	--	0.15	0.17	$\Omega$
Gate resistance	$R_G$	$f = 1.0\text{MHz}$ open drain	--	12	--	$\Omega$
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 100V,$ $f = 1.0\text{MHz}$	--	1724	--	$\mu F$
Output Capacitance	$C_{oss}$		--	61	--	
Reverse Transfer Capacitance	$C_{rss}$		--	6	--	
Total Gate Charge	$Q_g$	$V_{DD} = 520V, I_D = 20A,$ $V_{GS} = 10V$	--	38.5	--	nC
Gate-Source Charge	$Q_{gs}$		--	8	--	
Gate-Drain Charge	$Q_{gd}$		--	15	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 20A,$ $R_G = 25\Omega$	--	15	--	ns
Turn-on Rise Time	$t_r$		--	59	--	
Turn-off Delay Time	$t_{d(off)}$		--	121	--	
Turn-off Fall Time	$t_f$		--	44	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	20	A
Pulsed Diode Forward Current	$I_{SM}$		--	--	60	
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 20A, V_{GS} = 0V$	--	0.9	1.2	V
Reverse Recovery Time	$t_{rr}$	$V_R = 400V, I_F = I_S,$ $di_F/dt = 100A/\mu s$	--	423	--	ns
Reverse Recovery Charge	$Q_{rr}$		--	5.3	--	$\mu C$
Peak Reverse Recovery Current	$I_{rm}$		--	25	--	A

**Notes**

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2.  $I_{AS} = 3.5A, V_{DD} = 50V, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 1\%$



Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Output Characteristics

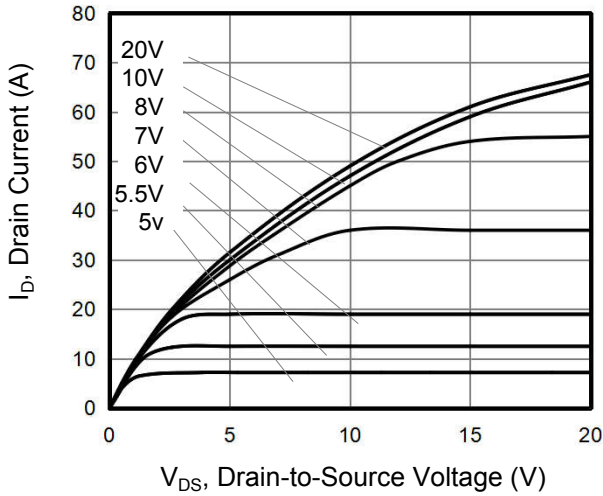


Figure 2. Transfer Characteristics

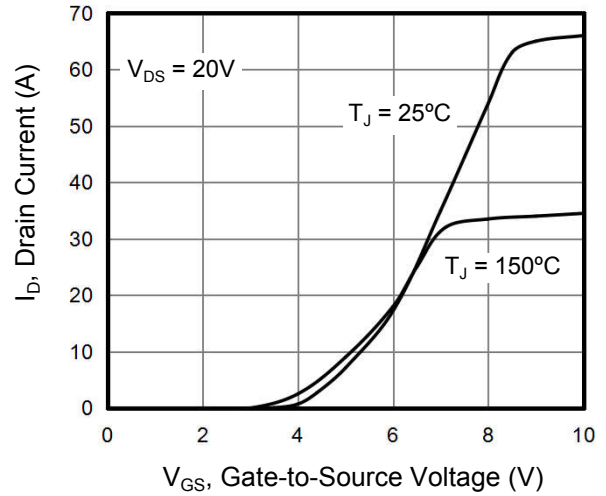


Figure 3. On-Resistance vs. Drain Current

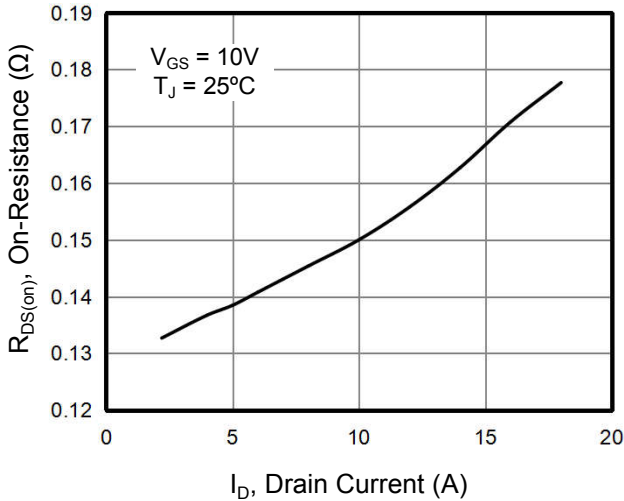


Figure 4. Capacitance

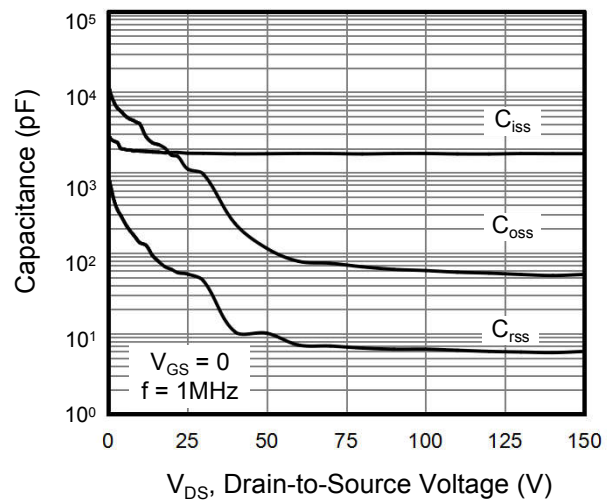


Figure 5. Gate Charge

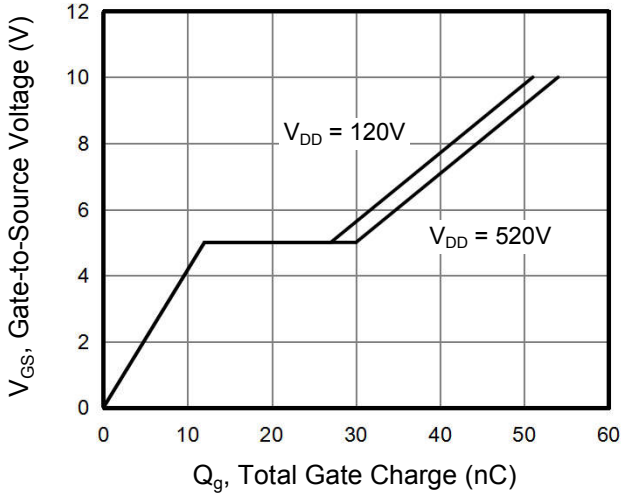
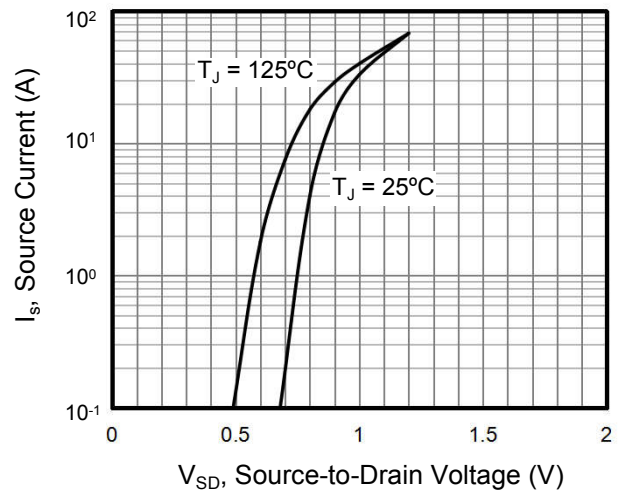


Figure 6. Body Diode Forward Voltage





Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

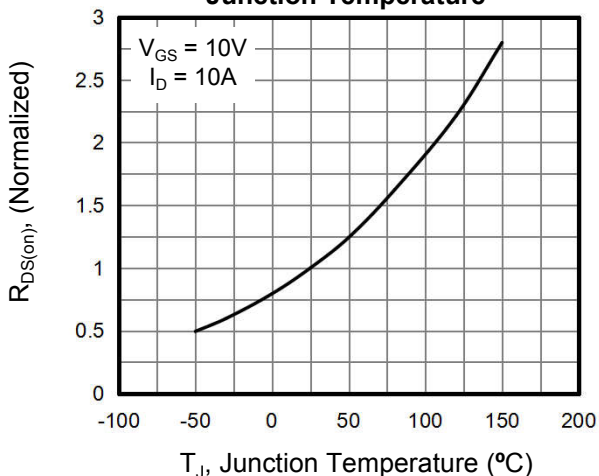


Figure 8. Threshold Voltage vs. Junction Temperature

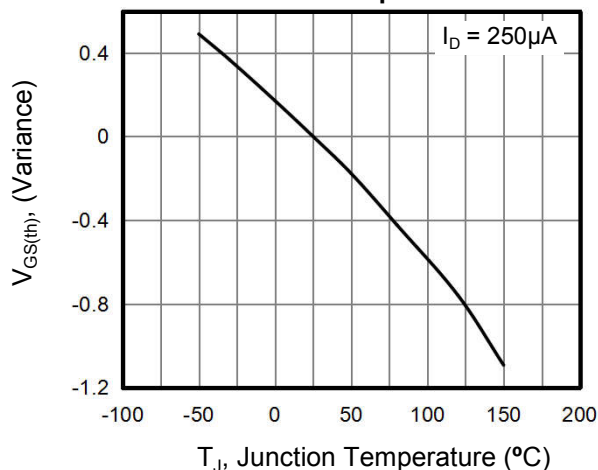


Figure 9. Transient Thermal Impedance TO-220/TO-3PN/TO-247

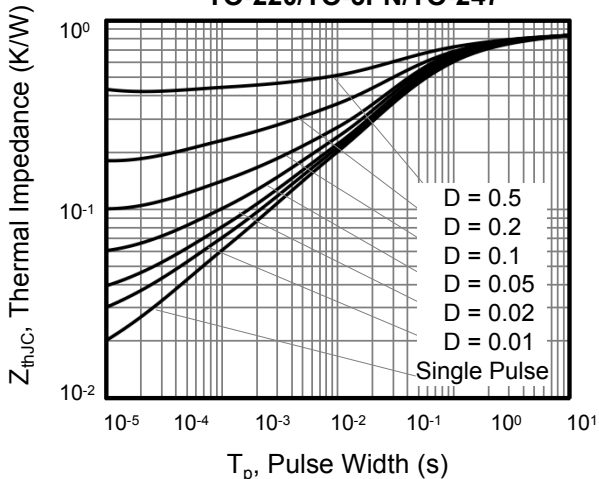


Figure 10. Transient Thermal Impedance TO-220F

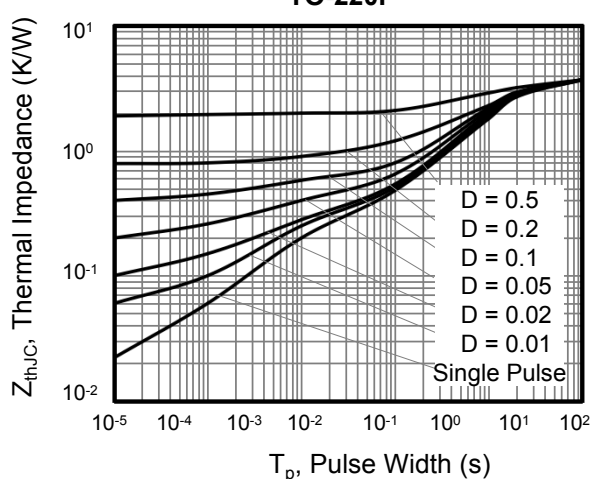


Figure 12. Safe operation area for TO-220/TO-3PN/TO-247

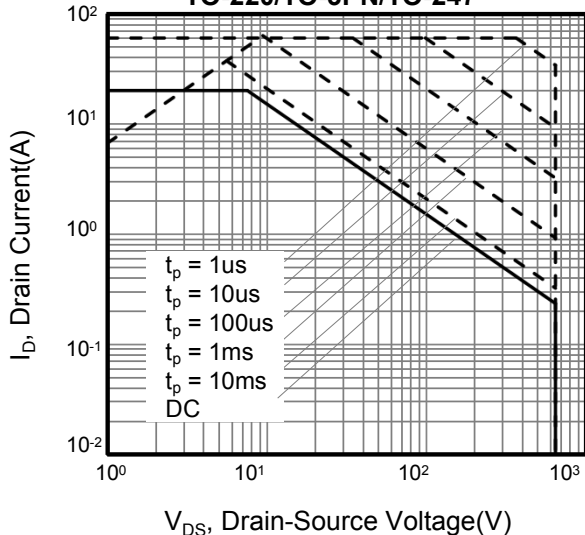


Figure 13. Safe operation area for TO-220F

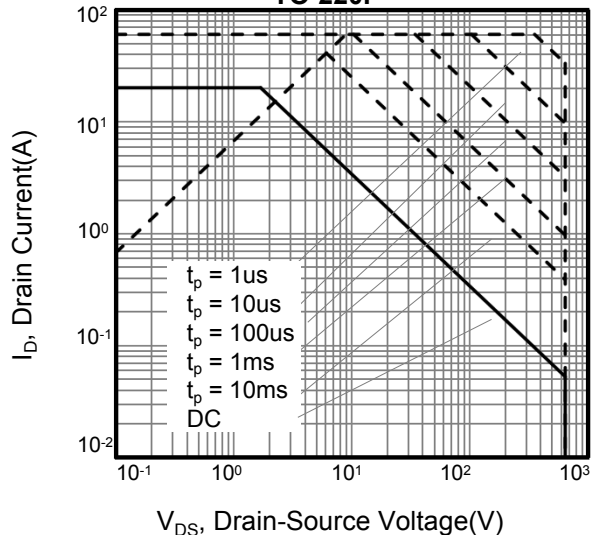




Figure A: Gate Charge Test Circuit and Waveform

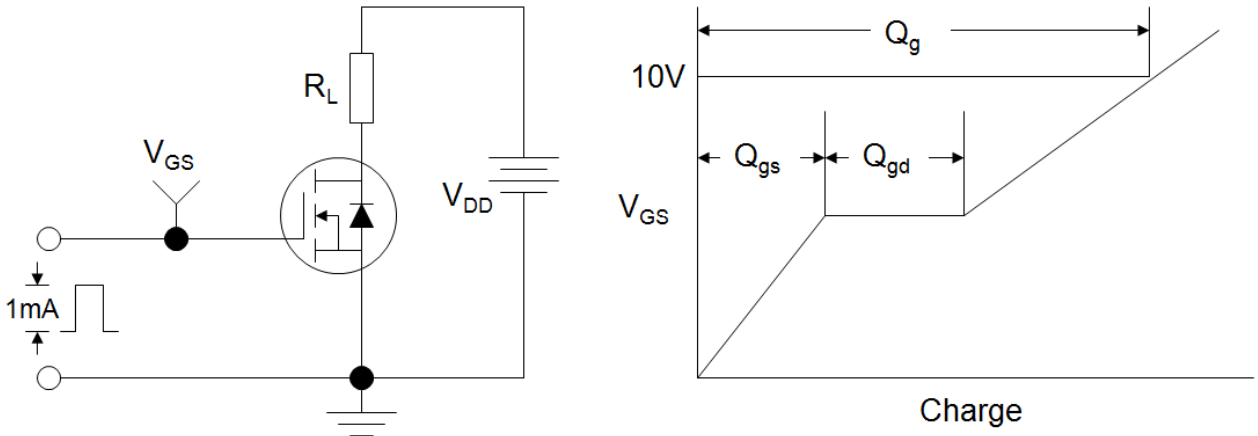


Figure B: Resistive Switching Test Circuit and Waveform

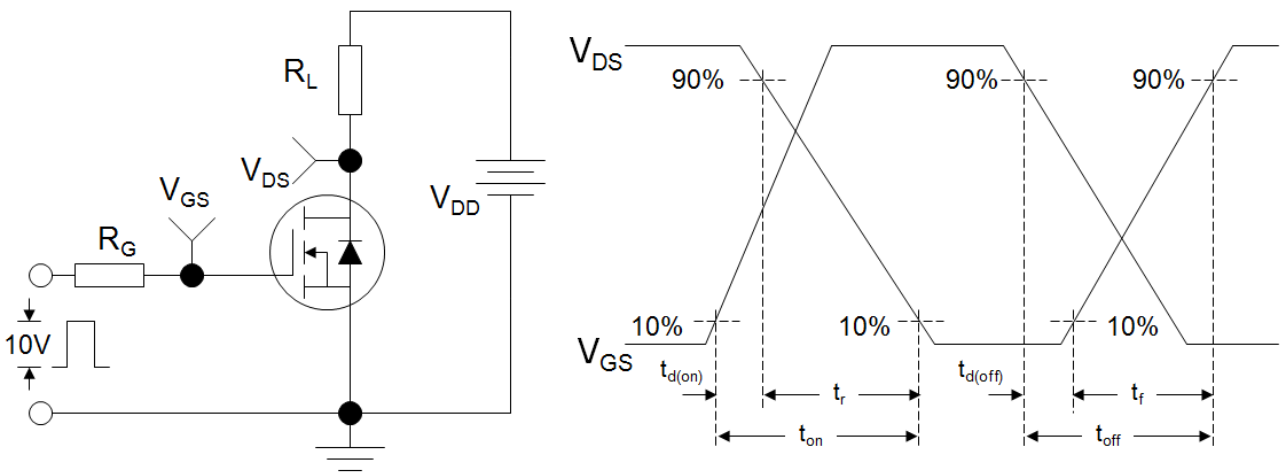
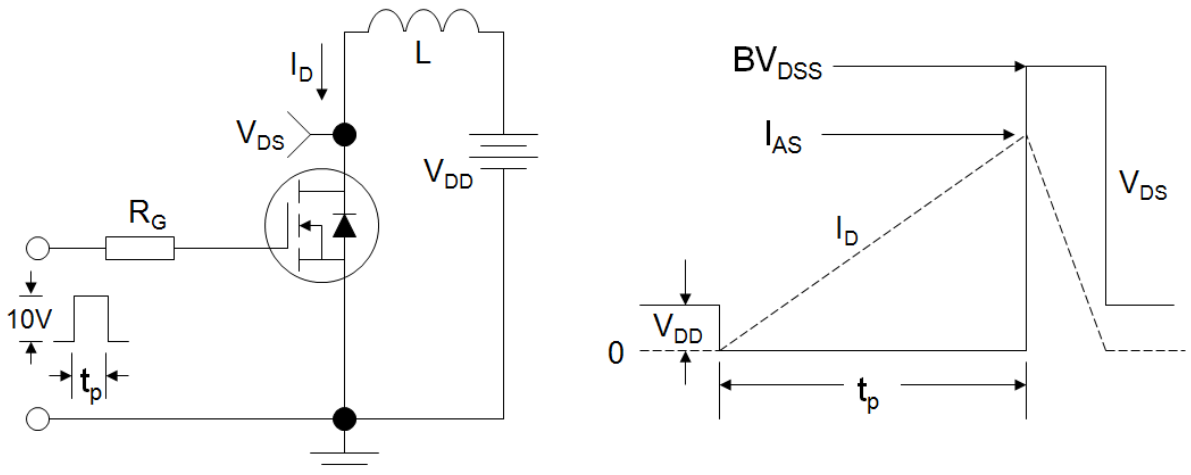
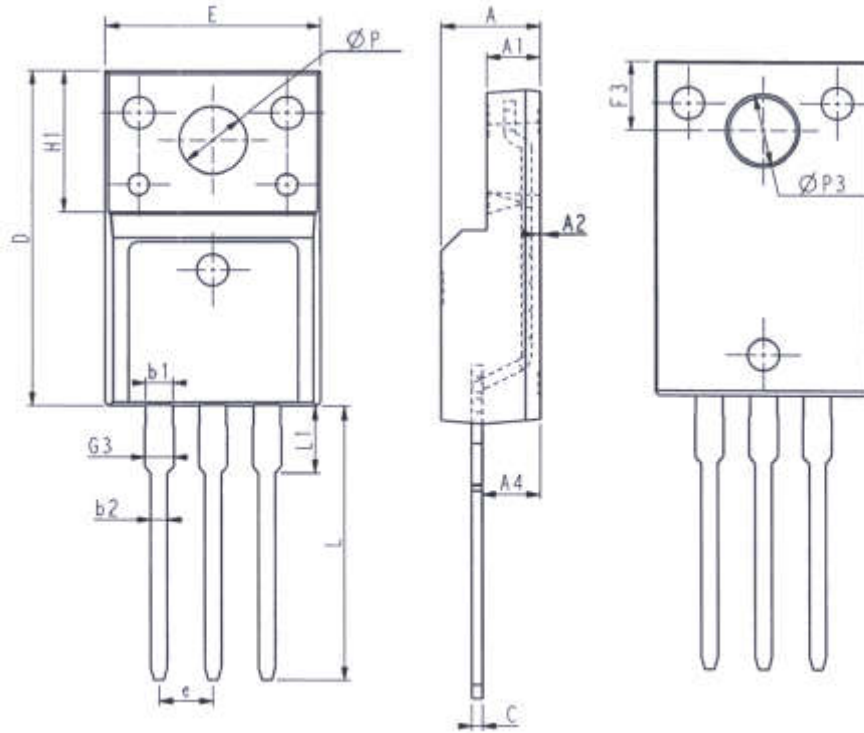


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





## TO-220F



Unit: mm			Unit: mm		
Symbol	Min.	Max.	Symbol	Min.	Max.
E	9.96	10.36	L	12.68	13.28
A	4.50	4.90	L1	2.93	3.13
A1	2.34	2.74	P	3.03	3.38
A2	0.30	0.60	P3	3.15	3.65
A4	2.56	2.96	F3	3.15	3.45
c	0.40	0.65	G3	1.25	1.55
D	15.57	16.17	b1	1.18	1.43
H1	6.70REF		b2	0.70	0.95
e	2.54BSC				